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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100bgana-u0

Table 1-1. List of Ordering Part Numbers

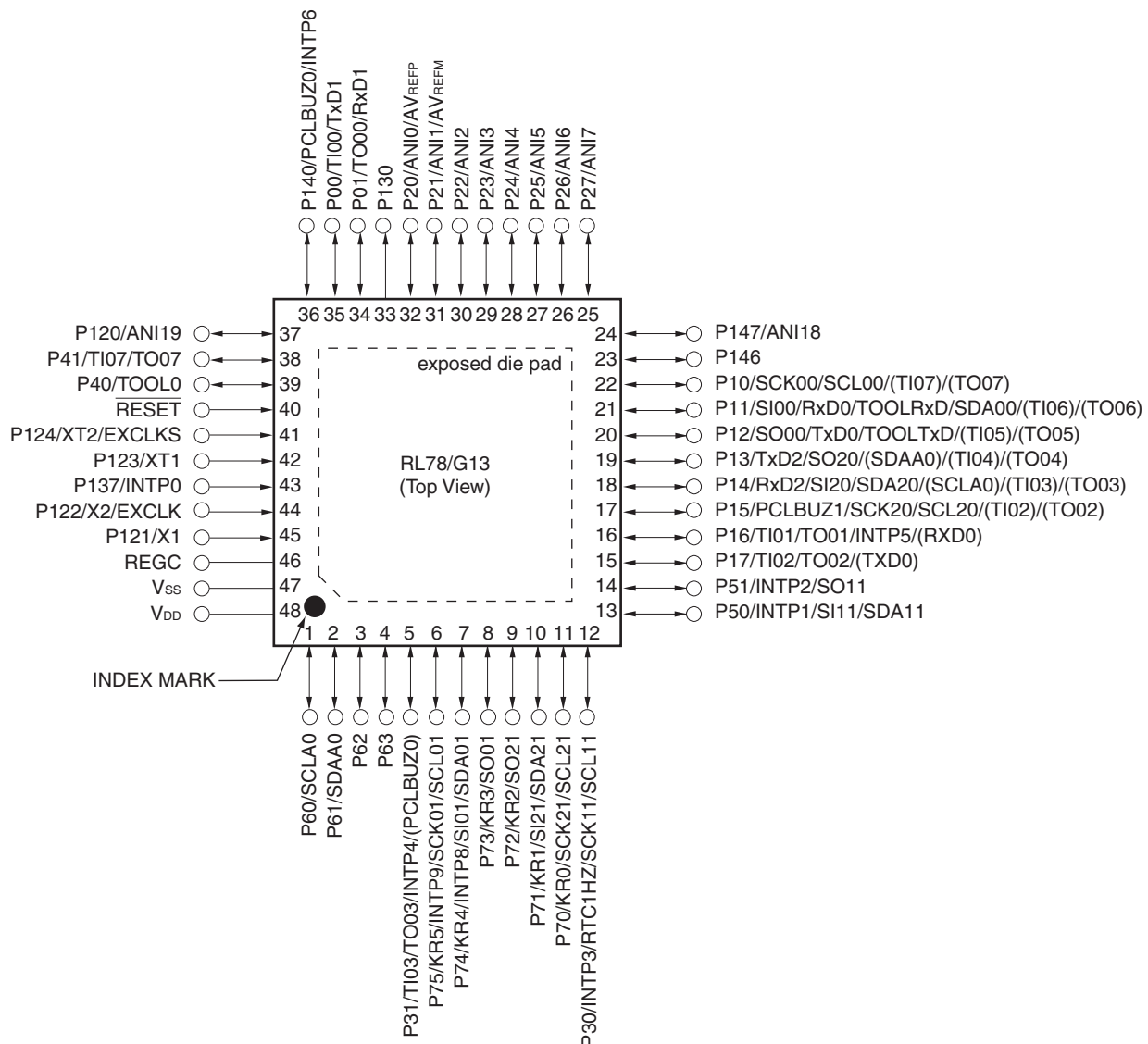
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Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CCALA#W0, R5F100CDALA#W0, R5F100CEALA#W0, R5F100CFALA#W0, R5F100CGALA#W0 R5F100CAGLA#U0, R5F100CCGLA#U0, R5F100CDGLA#U0, R5F100CEGLA#U0, R5F100CFGLA#U0, R5F100CGGLA#U0 R5F100CAGLA#W0, R5F100CCGLA#W0, R5F100CDGLA#W0, R5F100CEGLA#W0, R5F100CFGLA#W0, R5F100CGGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0, R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0, R5F100EHANA#W0 R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0 R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EGGNA#W0, R5F100EHGNA#W0
		Not mounted	A	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EFANA#W0, R5F101EGANA#W0, R5F101EHANA#W0 R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EFDNA#U0, R5F101EGDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EEDNA#W0, R5F101EFDNA#W0, R5F101EGDNA#W0, R5F101EHDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)

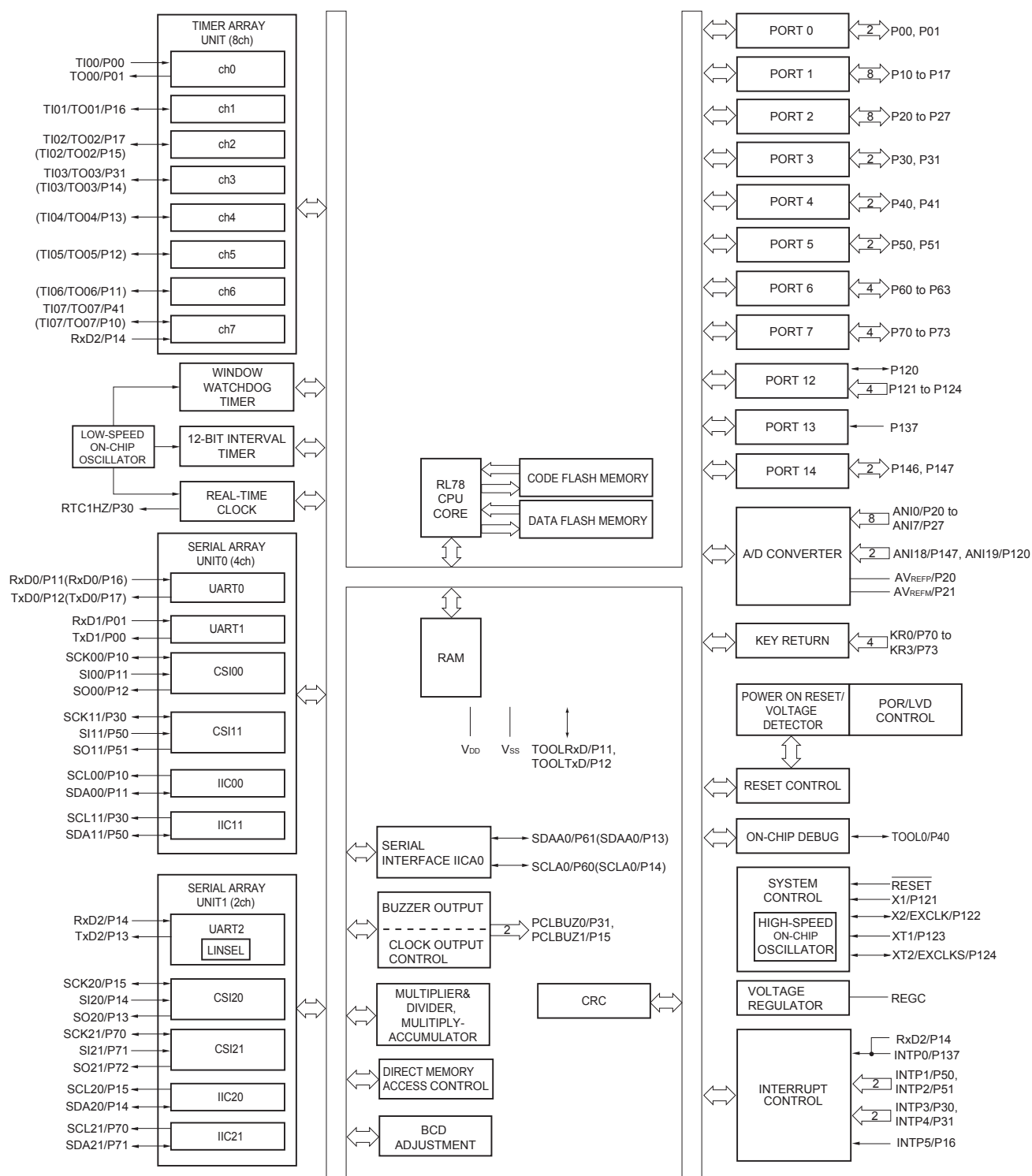


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
- It is recommended to connect an exposed die pad to Vss.

1.5.8 44-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

(2/2)

Item		80-pin		100-pin		128-pin	
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx
Clock output/buzzer output		2		2		2	
		<ul style="list-style-type: none">2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: $f_{\text{MAIN}} = 20 \text{ MHz}$ operation)256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: $f_{\text{SUB}} = 32.768 \text{ kHz}$ operation)					
8/10-bit resolution A/D converter		17 channels		20 channels		26 channels	
Serial interface		[80-pin, 100-pin, 128-pin products]					
		<ul style="list-style-type: none">CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channelCSI: 2 channels/simplified I²C: 2 channels/UART: 1 channelCSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channelCSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel					
	I ² C bus	2 channels		2 channels		2 channels	
Multiplier and divider/multiply-accumulator		<ul style="list-style-type: none">16 bits \times 16 bits = 32 bits (Unsigned or signed)32 bits \div 32 bits = 32 bits (Unsigned)16 bits \times 16 bits + 32 bits = 32 bits (Unsigned or signed)					
DMA controller		4 channels					
Vectored interrupt sources	Internal	37		37		41	
	External	13		13		13	
Key interrupt		8		8		8	
Reset		<ul style="list-style-type: none">Reset by $\overline{\text{RESET}}$ pinInternal reset by watchdog timerInternal reset by power-on-resetInternal reset by voltage detectorInternal reset by illegal instruction execution ^{Note}Internal reset by RAM parity errorInternal reset by illegal-memory access					
Power-on-reset circuit		<ul style="list-style-type: none">Power-on-reset: 1.51 V (TYP.)Power-down-reset: 1.50 V (TYP.)					
Voltage detector		<ul style="list-style-type: none">Rising edge : 1.67 V to 4.06 V (14 stages)Falling edge : 1.63 V to 3.98 V (14 stages)					
On-chip debug function		Provided					
Power supply voltage		$V_{\text{DD}} = 1.6 \text{ to } 5.5 \text{ V}$ ($T_{\text{A}} = -40 \text{ to } +85^{\circ}\text{C}$) $V_{\text{DD}} = 2.4 \text{ to } 5.5 \text{ V}$ ($T_{\text{A}} = -40 \text{ to } +105^{\circ}\text{C}$)					
Operating ambient temperature		$T_{\text{A}} = 40 \text{ to } +85^{\circ}\text{C}$ (A: Consumer applications, D: Industrial applications) $T_{\text{A}} = 40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications)					

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

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2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EV _{SS0} , EV _{SS1}	EV _{SS0} = EV _{SS1}	-0.5 to +0.3	V
REGC pin input voltage	V _{IREGC}	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	V _{I1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	V _{I3}	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Output voltage	V _{O1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Analog input voltage	V _{AI1}	ANI16 to ANI26	-0.3 to EV _{DD0} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V
	V _{AI2}	ANI0 to ANI14	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V

Notes 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

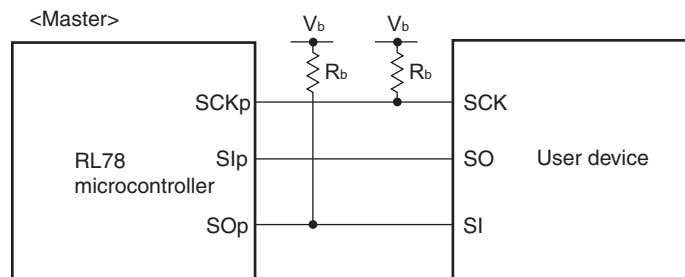
3. V_{SS} : Reference voltage

- Notes**
1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }8\text{ MHz}$
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }4\text{ MHz}$
 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH}: High-speed on-chip oscillator clock frequency
3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

- Notes**
1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 3. When high-speed system clock and subsystem clock are stopped.
 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V} @ 1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V} @ 1\text{ MHz to }16\text{ MHz}$
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V} @ 1\text{ MHz to }8\text{ MHz}$
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V} @ 1\text{ MHz to }4\text{ MHz}$

- Remarks**
1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH}: High-speed on-chip oscillator clock frequency
 3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

CSI mode connection diagram (during communication at different potential)

- Remarks**
1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 2. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number, n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number ($mn = 00$))
 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	t _{SU:DAT}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 135 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 135 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ	1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		1/f _{MCK} + 190 ^{Note 3}		kHz
Data hold time (transmission)	t _{HD:DAT}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.2. Use it with EV_{DD0} ≥ V_b.3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

- Notes**
1. Excludes quantization error ($\pm 1/2$ LSB).
 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 4. Values when the conversion time is set to $57\ \mu\text{s}$ (min.) and $95\ \mu\text{s}$ (max.).
 5. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

2.8 Flash Memory Programming Characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1		32	MHz
Number of code flash rewrites <small>Notes 1, 2, 3</small>	C_{erwr}	Retained for 20 years $T_A = 85^\circ\text{C}$	1,000			Times
Number of data flash rewrites <small>Notes 1, 2, 3</small>		Retained for 1 years $T_A = 25^\circ\text{C}$		1,000,000		
		Retained for 5 years $T_A = 85^\circ\text{C}$	100,000			
		Retained for 20 years $T_A = 85^\circ\text{C}$	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

Absolute Maximum Ratings ($T_A = 25^{\circ}\text{C}$) (2/2)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I _{OH1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	−40	mA
		Total of all pins −170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	−70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	−100	mA
	I _{OH2}	Per pin	P20 to P27, P150 to P156	−0.5	mA
		Total of all pins		−2	mA
	Output current, low	I _{OL1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40
Total of all pins 170 mA			P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
I _{OL2}		Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature		T _A	In normal operation mode		−40 to +105
	In flash memory programming mode				
Storage temperature	T _{stg}			−65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate		Reception	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$		$f_{MCK}/12$ ^{Note 1}	bps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6	Mbps
			$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$		$f_{MCK}/12$ ^{Note 1}	bps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6	Mbps
			$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$		$f_{MCK}/12$ ^{Notes 1,2}	bps
			Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		2.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2.** The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$.
 $2.4\text{ V} \leq EV_{DD0} < 2.7\text{ V}$: MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Remarks 1. $V_b[V]$: Communication line voltage**2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)**3.** f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp \uparrow) ^{Note}	t_{SIK1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	162		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	354		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	958		ns
Slp hold time (from SCKp \uparrow) ^{Note}	t_{KSI1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	38		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	38		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	38		ns
Delay time from SCKp \downarrow to SOp output ^{Note}	t_{KSO1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		200	ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		390	ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

- (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = $AV_{REFM}/ANI1$ (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{BGR} ^{Note 3}, Reference voltage (–) = AV_{REFM} ^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	t_{CONV}	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} ^{Note 3}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS} , the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM} .

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

3.6.2 Temperature sensor/internal reference voltage characteristics

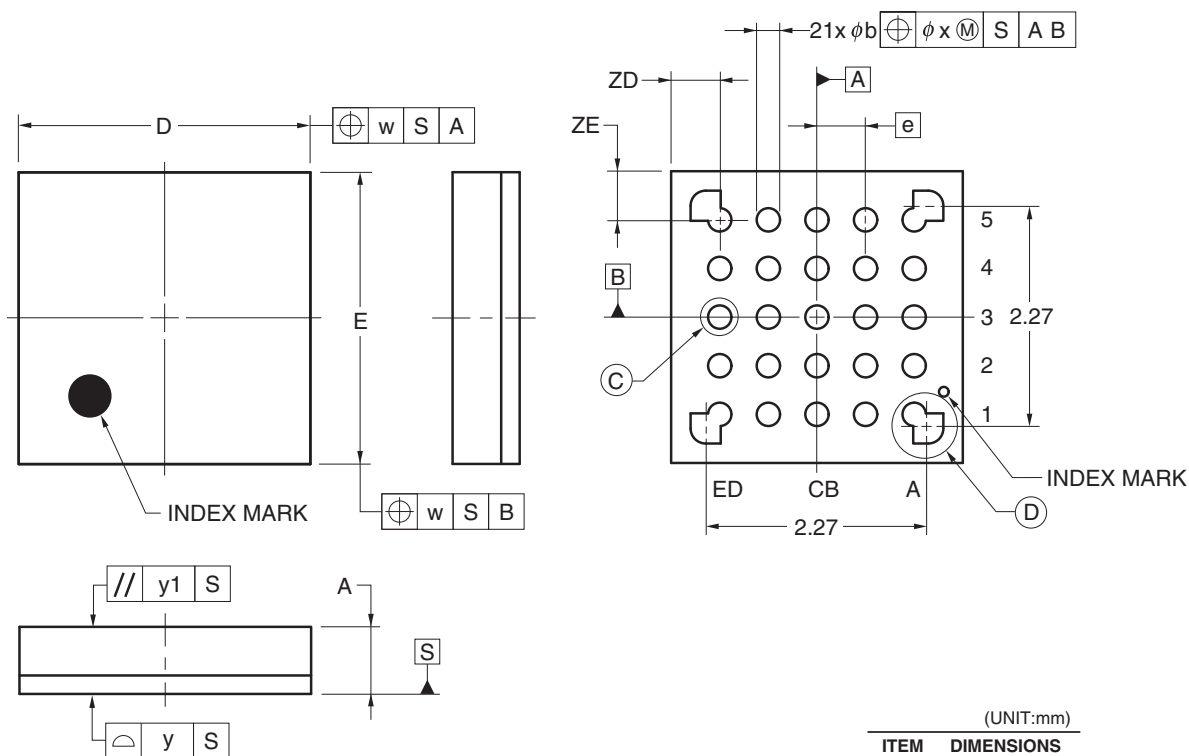
($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		–3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	t_{AMP}		5			μs

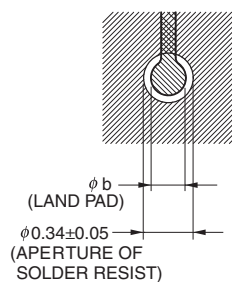
4.3 25-pin Products

R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA
R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA
R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA

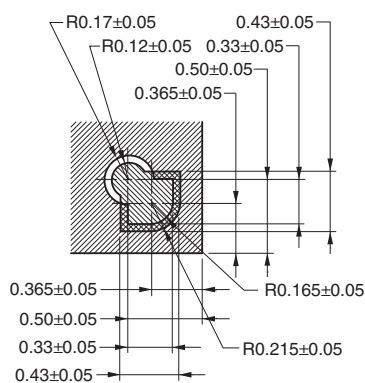
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



DETAIL OF © PART



DETAIL OF (D) PART



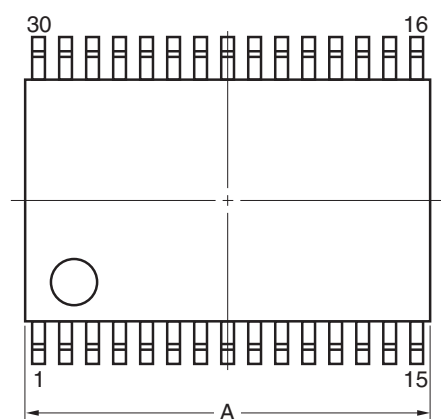
(UNIT:mm)	
ITEM	DIMENSIONS
D	3.00 ±0.10
E	3.00 ±0.10
w	0.20
e	0.50
A	0.69 ±0.07
b	0.24 ±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.50
ZE	0.50

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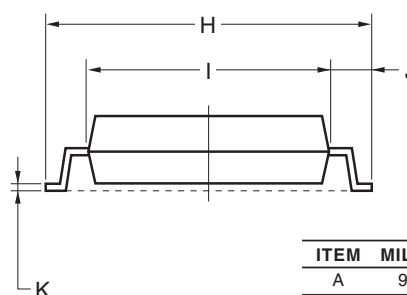
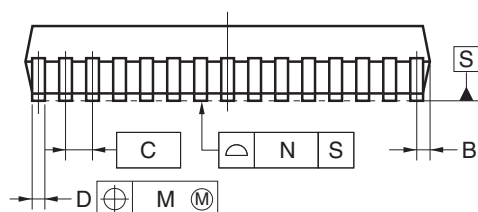
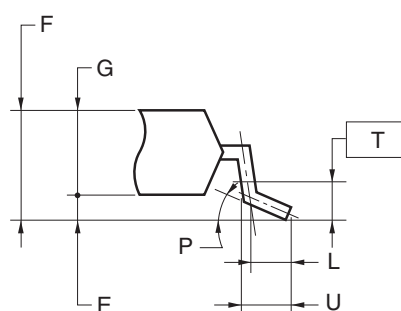
4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP
 R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP
 R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP
 R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP
 R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end

**NOTE**

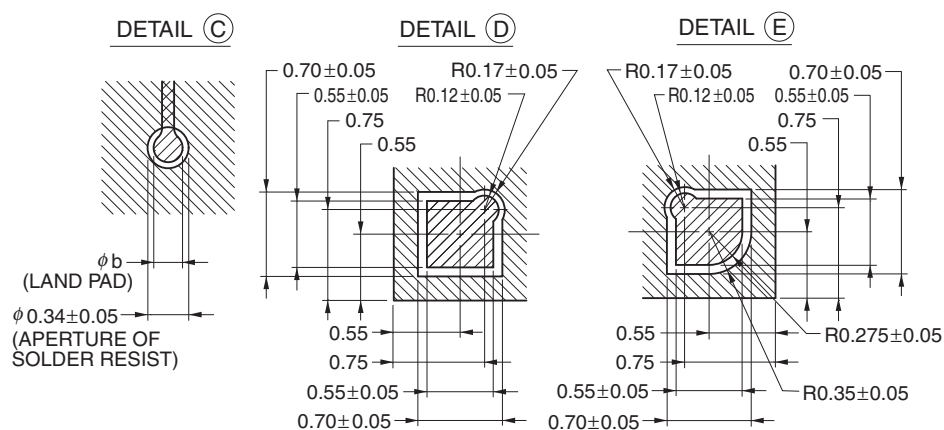
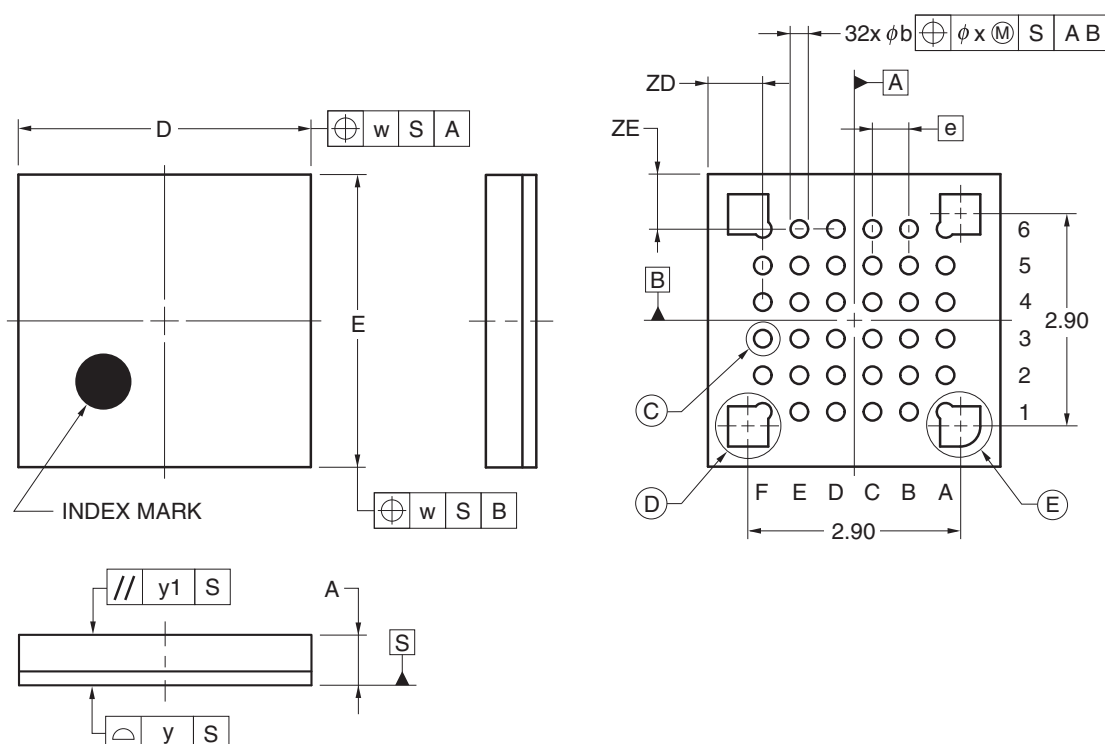
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

4.6 36-pin Products

R5F100CAALA, R5F100CCALA, R5F100CDALA, R5F100CEALA, R5F100CFALA, R5F100CGALA
 R5F101CAALA, R5F101CCALA, R5F101CDALA, R5F101CEALA, R5F101CFALA, R5F101CGALA
 R5F100CAGLA, R5F100CCGLA, R5F100CDGLA, R5F100CEGLA, R5F100CFGLA, R5F100CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



(UNIT:mm)

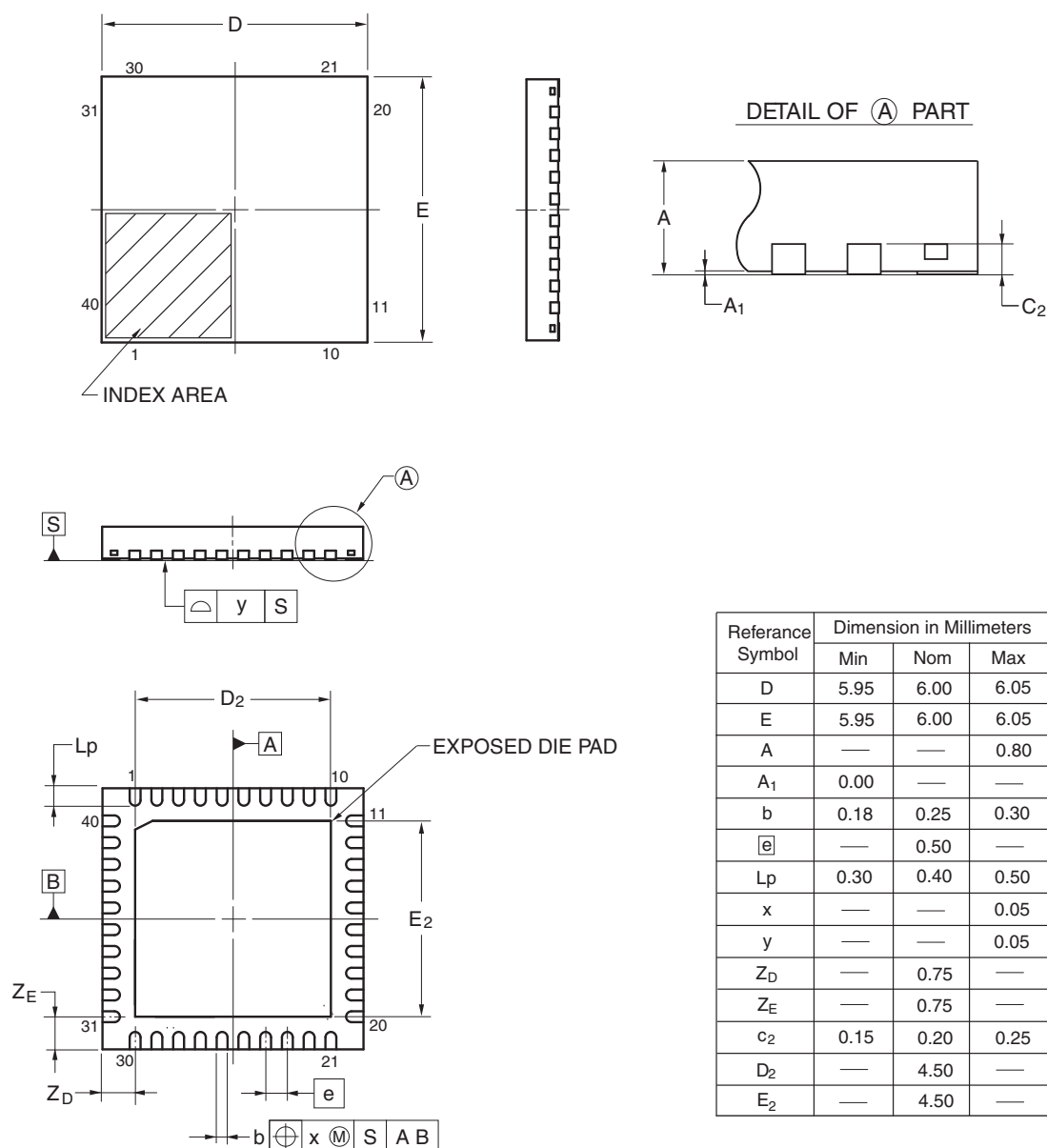
ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

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4.7 40-pin Products

R5F100EAANA, R5F100ECANA, R5F100EDANA, R5F100EEANA, R5F100EFANA, R5F100EGANA, R5F100EHANA
 R5F101EAANA, R5F101ECANA, R5F101EDANA, R5F101EEANA, R5F101EFANA, R5F101EGANA, R5F101EHANA
 R5F100EADNA, R5F100ECDNA, R5F100EDDNA, R5F100EEDNA, R5F100EFDNA, R5F100EGDNA,
 R5F100EHDNA
 R5F101EADNA, R5F101ECDNA, R5F101EDDNA, R5F101EEDNA, R5F101EFDNA, R5F101EGDNA,
 R5F101EHDNA
 R5F100EAGNA, R5F100ECGNA, R5F100EDGNA, R5F100EEGNA, R5F100EFGNA, R5F100EGGNA,
 R5F100EHGNA

JEITA Package code	RENESAS code	Previous code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09



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Revision History	RL78/G13 Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings ($T_A = 25^{\circ}\text{C}$)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing